

Title (en)

ION SOURCE CLEANING IN SEMICONDUCTOR PROCESSING SYSTEMS

Title (de)

IONENQUELLENREINIGUNG IN HALBLEITERVERARBEITUNGSSYSTEMEN

Title (fr)

NETTOYAGE DE SOURCE D'IONS DANS DES SYSTÈMES DE TRAITEMENT DE SEMI-CONDUCTEURS

Publication

**EP 2396809 A1 20111221 (EN)**

Application

**EP 09840155 A 20090812**

Priority

- US 2009053520 W 20090812
- US 2009033754 W 20090211

Abstract (en)

[origin: WO2010093380A1] Cleaning of an ion implantation system or components thereof, utilizing temperature and/or a reactive cleaning reagent enabling growth/etching of the cathode in an indirectly heated cathode for an ion implantation system by monitoring the cathode bias power and taking corrective action depending upon compared values to etch or regrow the cathode.

IPC 8 full level

**H01L 21/265** (2006.01)

CPC (source: CN EP KR)

**C23C 14/48** (2013.01 - CN EP KR); **C23C 14/54** (2013.01 - CN EP KR); **C23C 14/564** (2013.01 - CN EP KR); **H01J 27/08** (2013.01 - CN EP); **H01J 37/08** (2013.01 - CN EP KR); **H01J 37/16** (2013.01 - CN EP KR); **H01J 37/18** (2013.01 - CN EP); **H01J 37/3171** (2013.01 - CN EP KR); **H01J 37/32862** (2013.01 - CN EP KR); **H01J 2237/0209** (2013.01 - CN EP KR); **H01J 2237/022** (2013.01 - CN EP KR); **H01J 2237/082** (2013.01 - CN EP KR); **H01J 2237/22** (2013.01 - CN EP KR)

Citation (search report)

See references of WO 2010093380A1

Designated contracting state (EPC)

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DOCDB simple family (publication)

**WO 2010093380 A1 20100819**; CN 102396048 A 20120328; CN 102396048 B 20140827; CN 104217981 A 20141217; CN 104217981 B 20180109; EP 2396809 A1 20111221; KR 101658975 B1 20160923; KR 20110128848 A 20111130; SG 173621 A1 20110929; TW 201030792 A 20100816; TW 201438052 A 20141001; TW I463516 B 20141201; TW I567775 B 20170121

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**US 2009053520 W 20090812**; CN 200980158194 A 20090812; CN 201410367226 A 20090812; EP 09840155 A 20090812; KR 20117020918 A 20090812; SG 2011057536 A 20090812; TW 103120759 A 20090813; TW 98127518 A 20090813